

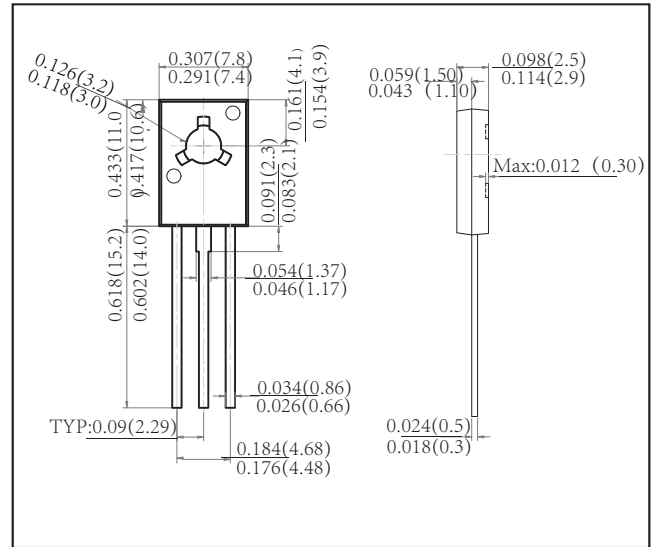
TO-18 Plastic-Encapsulate Transistors

FEATURES

- High Forward Current Transfer Ratio h_{FE} Which has Satisfactory Linearity
- Low Collector-Emitter Saturation Voltage $V_{CE(sat)}$
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-18 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

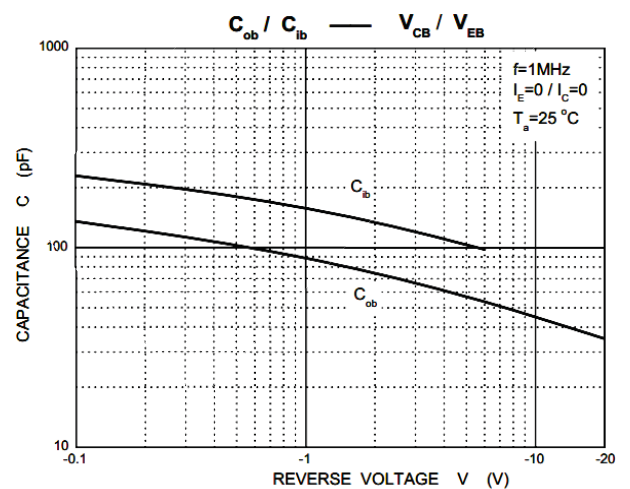
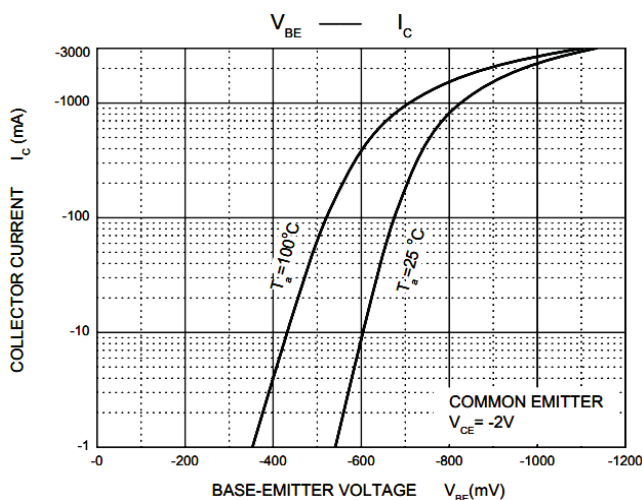
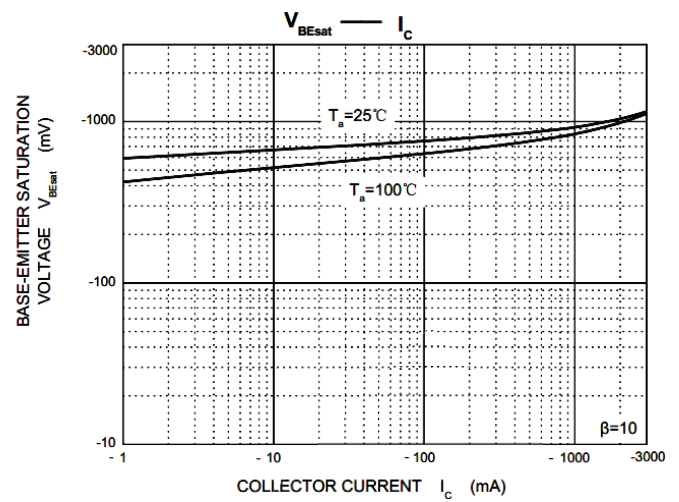
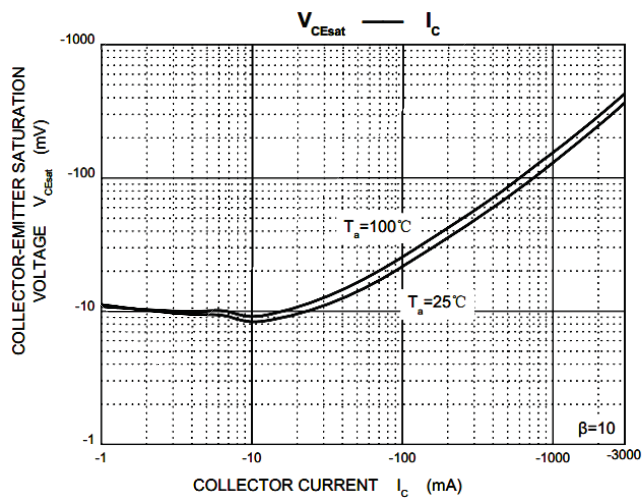
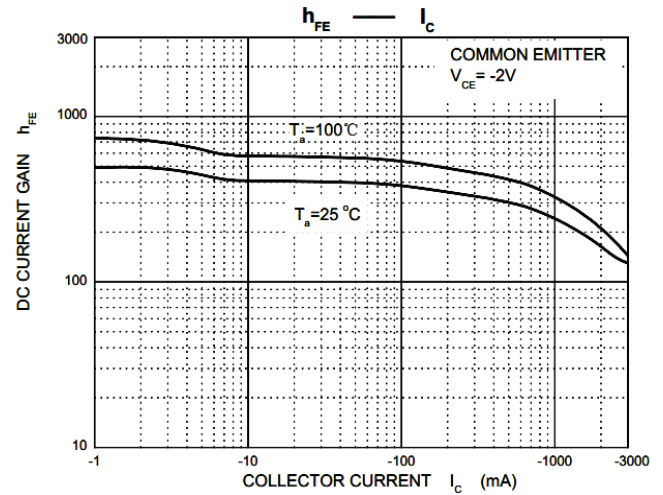
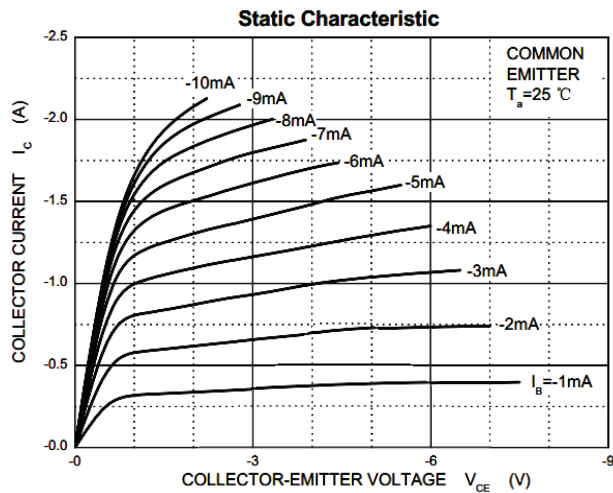
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	-40	V
Collector Emitter Voltage	V_{CEO}	-30	V
Emitter Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-3	A
Collector Power Dissipation	P_C	1.25	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	100	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 55 to +150	°C

MOSFET ELECTRICAL CHARACTERISTICS $T_A=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -30\text{V}, I_B = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -0.1\text{A}, f = 10\text{MHz}$	50	80		MHz

RATINGS AND CHARACTERISTIC CURVES



RATINGS AND CHARACTERISTIC CURVES

